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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, PWM, Voltage Detect, WDT
Number of I/O	75
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 20x10b; D/A 2x8b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f21388cnfp-v0

Table 1.2 Specifications for R8C/38C Group (2)

Item	Function	Specification
Timer	Timer RE	8 bits × 1 Real-time clock mode (count seconds, minutes, hours, days of week), output compare mode
	Timer RF	16 bits × 1 Input capture mode (input capture circuit), output compare mode (output compare circuit)
	Timer RG	16 bits × 1 (with 2 capture/compare registers) Timer mode (input capture function, output compare function), PWM mode (output 1 pin), phase counting mode (available automatic measurement for the counts of 2-phase encoder)
Serial Interface	UART0, UART1	Clock synchronous serial I/O/UART × 2 channel
	UART2	Clock synchronous serial I/O, UART, I^2C mode (I^2C bus), multiprocessor communication function
Synchronous Serial Communication Unit (SSU)		1 (shared with I^2C bus)
I^2C bus		1 (shared with SSU)
LIN Module		Hardware LIN: 1 (timer RA, UART0)
A/D Converter		10-bit resolution × 20 channels, includes sample and hold function, with sweep mode
D/A Converter		8-bit resolution × 2 circuits
Comparator B		2 circuits
Flash Memory		• Programming and erasure voltage: VCC = 2.7 to 5.5 V • Programming and erasure endurance: 10,000 times (data flash) 1,000 times (program ROM) • Program security: ROM code protect, ID code check • Debug functions: On-chip debug, on-board flash rewrite function • Background operation (BGO) function (data flash)
Operating Frequency/Supply Voltage		f(XIN) = 20 MHz (VCC = 2.7 to 5.5 V) f(XIN) = 5 MHz (VCC = 1.8 to 5.5 V)
Current consumption		Typ. 7.0 mA (VCC = 5.0 V, f(XIN) = 20 MHz) Typ. 3.5 mA (VCC = 3.0 V, f(XIN) = 10 MHz) Typ. 4.0 μA (VCC = 3.0 V, wait mode (f(XCIN) = 32 kHz)) Typ. 2.0 μA (VCC = 3.0 V, stop mode)
Operating Ambient Temperature		−20 to 85°C (N version) −40 to 85°C (D version) (1)
Package		80-pin LQFP Package code: PLQP0080KB-A (previous code: 80P6Q-A)

Note:
1. Specify the D version if D version functions are to be used.

Table 1.4 Pin Name Information by Pin Number (1)

Pin Number	Control Pin	Port	I/O Pin Functions for Peripheral Modules					
			Interrupt	Timer	Serial Interface	SSU	I^2C bus	A/D Converter, D/A Converter, Comparator B
1		P5_6		(TRAO/TRGIOA)				
2		P5_5		(TRAIO)				
3		P3_2	($\overline{INT1}$/ $\overline{INT2}$)	(TRAIO/TRGCLKB)				
4		P3_0		(TRAO/TRGCLKA)				
5		P4_2						VREF
6	MODE							
7	(XCIN)	P4_3						
8	(XCOUT)	P4_4						
9	$\overline{RESET}$							
10	XOUT	P4_7						
11	VSS/AVSS							
12	XIN	P4_6						
13	VCC/AVCC							
14		P5_4		(TRCIOD)				
15		P5_3		(TRCIOC)				
16		P5_2		(TRCIOB)				
17		P5_1		(TRCIOA/TRCTRG)				
18		P5_0		(TRCCLK)				
19		P3_7		TRAO	(TXD2/SDA2/ RXD2/SCL2)	SSO	SDA	
20		P3_5		(TRCIOD)	(CLK2)	SSCK	SCL	
21		P3_4		(TRCIOC)	(TXD2/SDA2/ RXD2/SCL2)	SSI		IVREF3
22		P3_3	$\overline{INT3}$	(TRCCLK)	($\overline{CTS2}$/$\overline{RTS2}$)	$\overline{SCS}$		IVCMP3
23		P2_7		(TRDIOD1)				
24		P2_6		(TRDIOC1)				
25		P2_5		(TRDIOB1)				
26		P2_4		(TRDIOA1)				
27		P2_3		(TRDIOD0)				
28		P2_2		(TRCIOD/TRDIOB0)				
29		P2_1		(TRCIOC/TRDIOC0)				
30		P2_0	($\overline{INT1}$)	(TRCIOB/TRDIOA0/ TRDCLK)				
31		P9_3						
32		P9_2						
33		P9_1						
34		P9_0						
35		P3_6	($\overline{INT1}$)					
36		P3_1		(TRBO)				
37		P8_7						
38		P8_6						
39		P8_5		(TRFO12)				
40		P8_4		(TRFO11)				

Note:
1. Can be assigned to the pin in parentheses by a program.

Table 1.7 Pin Functions (2)

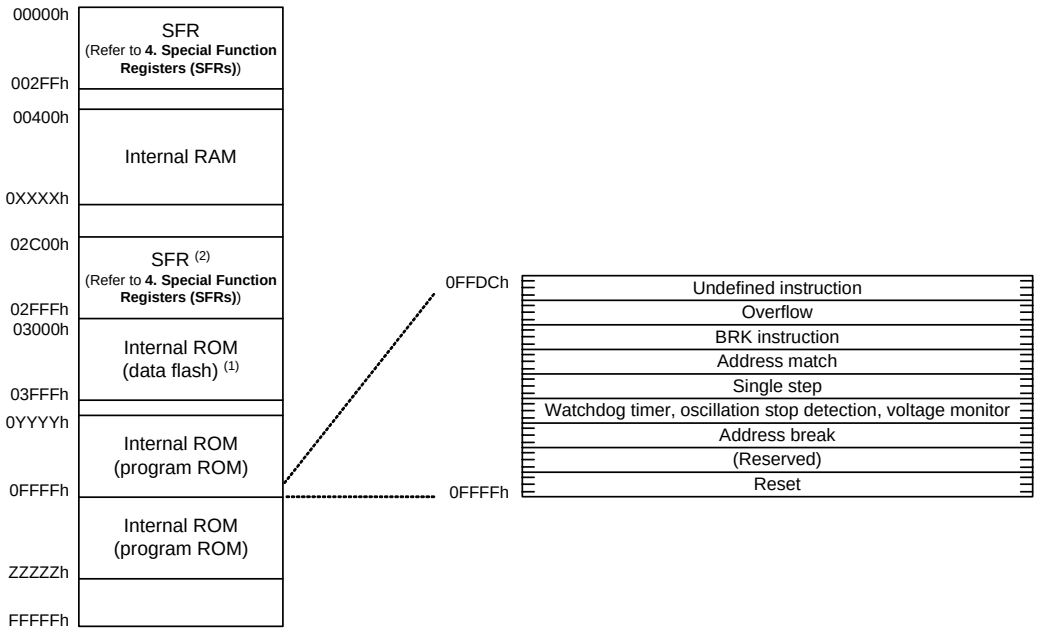
Item	Pin Name	I/O Type	Description
SSU	SSI	I/O	Data I/O pin.
	$\overline{SCS}$	I/O	Chip-select signal I/O pin.
	SSCK	I/O	Clock I/O pin.
	SSO	I/O	Data I/O pin.
I^2C bus	SCL	I/O	Clock I/O pin
	SDA	I/O	Data I/O pin
Reference voltage input	VREF	I	Reference voltage input pin to A/D converter.
A/D converter	AN0 to AN19	I	Analog input pins to A/D converter.
	$\overline{ADTRG}$	I	AD external trigger input pin.
D/A converter	DA0, DA1	O	D/A converter output pins.
Comparator B	IVCMP1, IVCMP3	I	Comparator B analog voltage input pins.
	IVREF1, IVREF3	I	Comparator B reference voltage input pins.
I/O port	P0_0 to P0_7, P1_0 to P1_7, P2_0 to P2_7, P3_0 to P3_7, P4_3 to P4_7, P5_0 to P5_7, P6_0 to P6_7, P7_0 to P7_7, P8_0 to P8_7, P9_0 to P9_5	I/O	CMOS I/O ports. Each port has an I/O select direction register, allowing each pin in the port to be directed for input or output individually. Any port set to input can be set to use a pull-up resistor or not by a program.
Input port	P4_2	I	Input-only port.

I: Input O: Output I/O: Input and output

3. Memory

3.1 R8C/38C Group

Figure 3.1 is a Memory Map of R8C/38C Group. The R8C/38C Group has a 1-Mbyte address space from addresses 00000h to FFFFFh. The internal ROM (program ROM) is allocated lower addresses, beginning with address 0FFFFh. For example, a 64-Kbyte internal ROM area is allocated addresses 04000h to 13FFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. The starting address of each interrupt routine is stored here.
The internal ROM (data flash) is allocated addresses 03000h to 03FFFh.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 6-Kbyte internal RAM area is allocated addresses 00400h to 01BFFh. The internal RAM is used not only for data storage but also as a stack area when a subroutine is called or when an interrupt request is acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh and 02C00h to 02FFFh (the SFR areas for the DTC and other modules). Peripheral function control registers are allocated here. All unallocated spaces within the SFRs are reserved and cannot be accessed by users.



Notes:
1. The data flash indicates block A (1 Kbyte), block B (1 Kbyte), block C (1 Kbyte), and block D (1 Kbyte).
2. The SFR areas for the DTC and other modules are allocated to addresses 02C00h to 02FFFh.
3. The blank areas are reserved and cannot be accessed by users.

Part Number	Internal ROM			Internal RAM	
	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh
R5F21386CNFP, R5F21386CDFP, R5F21386CNXXXFP, R5F21386CDXXXFP	32 Kbytes	08000h	–	2.5 Kbytes	00DFFh
R5F21387CNFP, R5F21387CDFP, R5F21387CNXXXFP, R5F21387CDXXXFP	48 Kbytes	04000h	–	4 Kbytes	013FFh
R5F21388CNFP, R5F21388CDFP, R5F21388CNXXXFP, R5F21388CDXXXFP	64 Kbytes	04000h	13FFFh	6 Kbytes	01BFFh
R5F2138ACNFP, R5F2138ACDFP, R5F2138ACNXXXFP, R5F2138ACDXXXFP	96 Kbytes	04000h	1BFFFh	8 Kbytes	023FFh
R5F2138CCNFP, R5F2138CCDFP, R5F2138CCNXXXFP, R5F2138CCDXXXFP	128 Kbytes	04000h	23FFFh	10 Kbytes	02BFFh

Figure 3.1 Memory Map of R8C/38C Group

Table 4.7 SFR Information (7) (1)

Address	Register	Symbol	After Reset
0180h	Timer RA Pin Select Register	TRASR	00h
0181h	Timer RB/RC Pin Select Register	TRBRCSR	00h
0182h	Timer RC Pin Select Register 0	TRCPSR0	00h
0183h	Timer RC Pin Select Register 1	TRCPSR1	00h
0184h	Timer RD Pin Select Register 0	TRDPSR0	00h
0185h	Timer RD Pin Select Register 1	TRDPSR1	00h
0186h	Timer Pin Select Register	TIMSR	00h
0187h	Timer RF Output Control Register	TRFOUT	00h
0188h	UART0 Pin Select Register	U0SR	00h
0189h	UART1 Pin Select Register	U1SR	00h
018Ah	UART2 Pin Select Register 0	U2SR0	00h
018Bh	UART2 Pin Select Register 1	U2SR1	00h
018Ch	SSU/IIC Pin Select Register	SSUIICSR	00h
018Dh			
018Eh	INT Interrupt Input Pin Select Register	INTSR	00h
018Fh	I/O Function Pin Select Register	PINSR	00h
0190h			
0191h			
0192h			
0193h	SS Bit Counter Register	SSBR	11111000b
0194h	SS Transmit Data Register L / IIC bus Transmit Data Register (2)	SSTDR / ICDRT	FFh
0195h	SS Transmit Data Register H (2)	SSTDRH	FFh
0196h	SS Receive Data Register L / IIC bus Receive Data Register (2)	SSRDR / ICDRR	FFh
0197h	SS Receive Data Register H (2)	SSRDRH	FFh
0198h	SS Control Register H / IIC bus Control Register 1 (2)	SSCRH / ICCR1	00h
0199h	SS Control Register L / IIC bus Control Register 2 (2)	SSCRL / ICCR2	01111101b
019Ah	SS Mode Register / IIC bus Mode Register (2)	SSMR / ICMR	00010000b / 00011000b
019Bh	SS Enable Register / IIC bus Interrupt Enable Register (2)	SSER / ICIER	00h
019Ch	SS Status Register / IIC bus Status Register (2)	SSSR / ICSR	00h / 0000X000b
019Dh	SS Mode Register 2 / Slave Address Register (2)	SSMR2 / SAR	00h
019Eh			
019Fh			
01A0h			
01A1h			
01A2h			
01A3h			
01A4h			
01A5h			
01A6h			
01A7h			
01A8h			
01A9h			
01AAh			
01ABh			
01ACh			
01ADh			
01AEh			
01AFh			
01B0h			
01B1h			
01B2h	Flash Memory Status Register	FST	10000X00b
01B3h			
01B4h	Flash Memory Control Register 0	FMR0	00h
01B5h	Flash Memory Control Register 1	FMR1	00h
01B6h	Flash Memory Control Register 2	FMR2	00h
01B7h			
01B8h			
01B9h			
01BAh			
01BBh			
01BCh			
01BDh			
01BEh			
01BFh			

X: Undefined

Notes:

1. The blank areas are reserved and cannot be accessed by users.
2. Selectable by the IICSEL bit in the SSUIICSR register.

Table 4.11 SFR Information (11) (1)

Address	Register	Symbol	After Reset
2CB0h	DTC Control Data 14	DTCD14	XXh
2CB1h			XXh
2CB2h			XXh
2CB3h			XXh
2CB4h			XXh
2CB5h			XXh
2CB6h			XXh
2CB7h			XXh
2CB8h	DTC Control Data 15	DTCD15	XXh
2CB9h			XXh
2CBAh			XXh
2CBBh			XXh
2CBCh			XXh
2CBDh			XXh
2CBEh			XXh
2CBFh			XXh
2CC0h	DTC Control Data 16	DTCD16	XXh
2CC1h			XXh
2CC2h			XXh
2CC3h			XXh
2CC4h			XXh
2CC5h			XXh
2CC6h			XXh
2CC7h			XXh
2CC8h	DTC Control Data 17	DTCD17	XXh
2CC9h			XXh
2CCAh			XXh
2CCBh			XXh
2CCCh			XXh
2CCDh			XXh
2CCEh			XXh
2CCFh			XXh
2CD0h	DTC Control Data 18	DTCD18	XXh
2CD1h			XXh
2CD2h			XXh
2CD3h			XXh
2CD4h			XXh
2CD5h			XXh
2CD6h			XXh
2CD7h			XXh
2CD8h	DTC Control Data 19	DTCD19	XXh
2CD9h			XXh
2CDAh			XXh
2CDBh			XXh
2CDCh			XXh
2CDDh			XXh
2CDEh			XXh
2CDFh			XXh
2CE0h	DTC Control Data 20	DTCD20	XXh
2CE1h			XXh
2CE2h			XXh
2CE3h			XXh
2CE4h			XXh
2CE5h			XXh
2CE6h			XXh
2CE7h			XXh
2CE8h	DTC Control Data 21	DTCD21	XXh
2CE9h			XXh
2CEAh			XXh
2CEBh			XXh
2CECh			XXh
2CEDh			XXh
2CEEh			XXh
2CEFh			XXh

X: Undefined

Note:

1. The blank areas are reserved and cannot be accessed by users.

5. Electrical Characteristics

Table 5.1 Absolute Maximum Ratings

Symbol	Parameter	Condition	Rated Value	Unit
V_{CC}/AV_{CC}	Supply voltage		–0.3 to 6.5	V
V_I	Input voltage		–0.3 to V_{CC} + 0.3	V
V_O	Output voltage		–0.3 to V_{CC} + 0.3	V
P_d	Power dissipation	$-40°C \leq T_{opr} \leq 85°C$	500	mW
T_{opr}	Operating ambient temperature		–20 to 85 (N version)/ –40 to 85 (D version)	°C
T_{stg}	Storage temperature		–65 to 150	°C

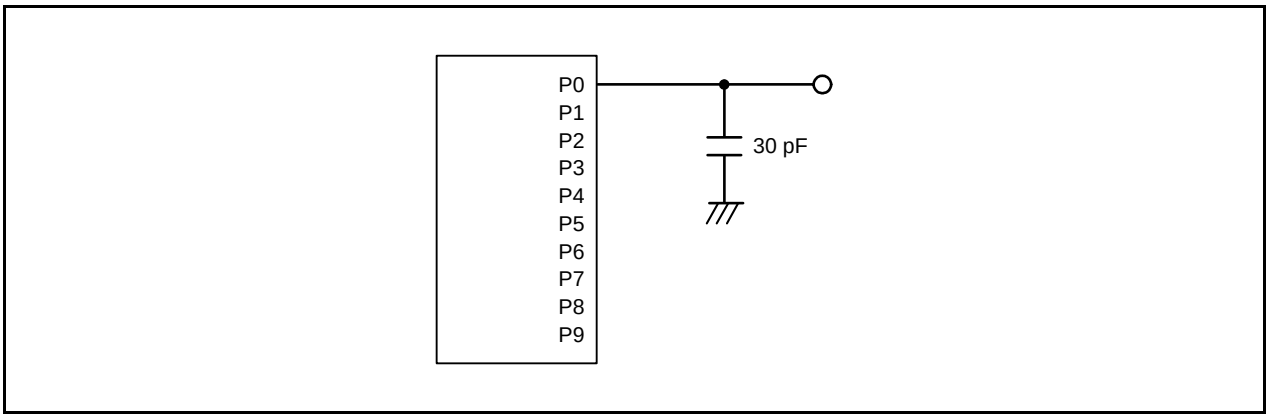


Figure 5.1 Ports P0 to P9 Timing Measurement Circuit

Table 5.3 A/D Converter Characteristics

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
—	Resolution		V_{ref} = AV_{CC}		—	—	10	Bit
—	Absolute accuracy	10-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±3	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±5	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±5	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±5	LSB
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
			V_{ref} = AV_{CC} = 3.3 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
			V_{ref} = AV_{CC} = 3.0 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
			V_{ref} = AV_{CC} = 2.2 V	AN0 to AN7 input, AN8 to AN11 input, AN12 to AN19 input	—	—	±2	LSB
ϕAD	A/D conversion clock		4.0 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	20	MHz
			3.2 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	16	MHz
			2.7 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	10	MHz
			2.2 V ≤ V_{ref} = AV_{CC} ≤ 5.5 V (2)		2	—	5	MHz
—	Tolerance level impedance				—	3	—	kΩ
t_{CONV}	Conversion time	10-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	—	—	µs
		8-bit mode	V_{ref} = AV_{CC} = 5.0 V, ϕAD = 20 MHz		2.2	—	—	µs
t_{SAMP}	Sampling time		ϕAD = 20 MHz		0.8	—	—	µs
I_{Vref}	V_{ref} current		V_{CC} = 5.0 V, XIN = f1 = ϕAD = 20 MHz		—	45	—	µA
V_{ref}	Reference voltage				2.2	—	AV_{CC}	V
V_{IA}	Analog input voltage (3)				0	—	V_{ref}	V
OCVREF	On-chip reference voltage		2 MHz ≤ ϕAD ≤ 4 MHz		1.19	1.34	1.49	V

Notes:
1. V_{CC}/AV_{CC} = V_{ref} = 2.2 to 5.5 V, V_{SS} = 0 V, and T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.
2. The A/D conversion result will be undefined in wait mode, stop mode, when the flash memory stops, and in low-current-consumption mode. Do not perform A/D conversion in these states or transition to these states during A/D conversion.
3. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.6 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance (2)		1,000 (3)	—	—	times
—	Byte program time		—	80	500	µs
—	Block erase time		—	0.3	—	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		—	—	5 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	µs
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly stopped until reading is enabled		–	–	30 + CPU clock × 1 cycle	µs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		0	—	60	°C
—	Data hold time (7)	Ambient temperature = 55 °C	20	—	—	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = 0 to 60 °C, unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed.)
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.7 Flash Memory (Data flash Block A to Block D) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
—	Program/erase endurance (2)		10,000 (3)	—	—	times
—	Byte program time (program/erase endurance ≤ 1,000 times)		—	160	1500	µs
—	Byte program time (program/erase endurance > 1,000 times)		—	300	1500	µs
—	Block erase time (program/erase endurance ≤ 1,000 times)		—	0.2	1	s
—	Block erase time (program/erase endurance > 1,000 times)		—	0.3	1	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		—	—	5 + CPU clock × 3 cycles	ms
—	Interval from erase start/restart until following suspend request		0	—	—	µs
—	Time from suspend until erase restart		—	—	30 + CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly stopped until reading is enabled		–	–	30 + CPU clock × 1 cycle	µs
—	Program, erase voltage		2.7	—	5.5	V
—	Read voltage		1.8	—	5.5	V
—	Program, erase temperature		–20 (7)	—	85	°C
—	Data hold time (8)	Ambient temperature = 55 °C	20	—	—	year

Notes:
1. V_{CC} = 2.7 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed.)
4. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A to D can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. –40 °C for D version.
8. The data hold time includes time that the power supply is off or the clock is not supplied.

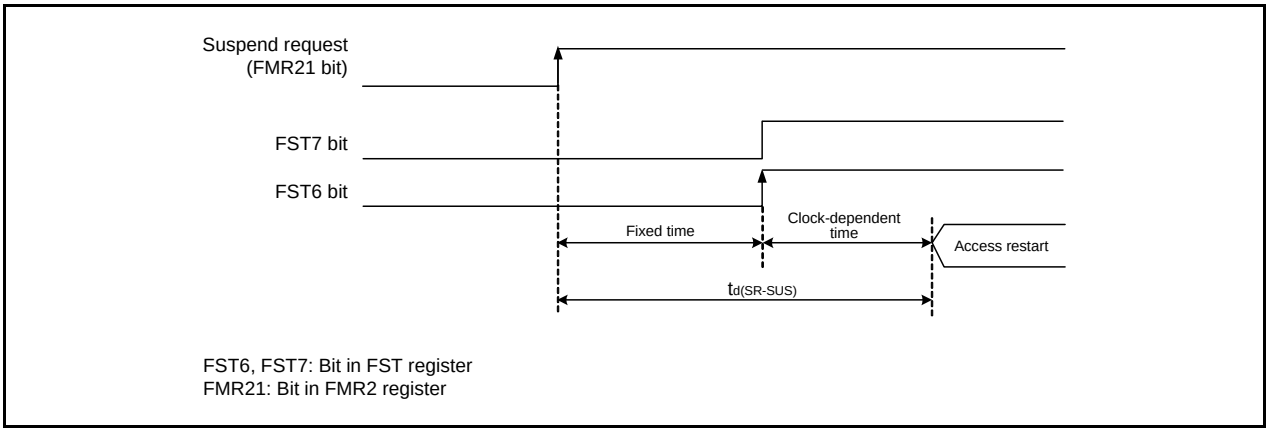


Figure 5.2 Time delay until Suspend

Table 5.8 Voltage Detection 0 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det0}	Voltage detection level Vdet0_0 (2)		1.80	1.90	2.05	V
	Voltage detection level Vdet0_1 (2)		2.15	2.35	2.50	V
	Voltage detection level Vdet0_2 (2)		2.70	2.85	3.05	V
	Voltage detection level Vdet0_3 (2)		3.55	3.80	4.05	V
—	Voltage detection 0 circuit response time (4)	At the falling of V_{CC} from 5.0 V to (Vdet0_0 – 0.1) V	—	6	150	µs
—	Voltage detection circuit self power consumption	VCA25 = 1, V_{CC} = 5.0 V	—	1.5	—	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (3)		—	—	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version).
2. Select the voltage detection level with bits VDSEL0 and VDSEL1 in the OFS register.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA25 bit in the VCA2 register to 0.
4. Time until the voltage monitor 0 reset is generated after the voltage passes V_{det0}.

Table 5.9 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level Vdet1_0 (2)	At the falling of V_{CC}	2.00	2.20	2.40	V
	Voltage detection level Vdet1_1 (2)	At the falling of V_{CC}	2.15	2.35	2.55	V
	Voltage detection level Vdet1_2 (2)	At the falling of V_{CC}	2.30	2.50	2.70	V
	Voltage detection level Vdet1_3 (2)	At the falling of V_{CC}	2.45	2.65	2.85	V
	Voltage detection level Vdet1_4 (2)	At the falling of V_{CC}	2.60	2.80	3.00	V
	Voltage detection level Vdet1_5 (2)	At the falling of V_{CC}	2.75	2.95	3.15	V
	Voltage detection level Vdet1_6 (2)	At the falling of V_{CC}	2.85	3.10	3.40	V
	Voltage detection level Vdet1_7 (2)	At the falling of V_{CC}	3.00	3.25	3.55	V
	Voltage detection level Vdet1_8 (2)	At the falling of V_{CC}	3.15	3.40	3.70	V
	Voltage detection level Vdet1_9 (2)	At the falling of V_{CC}	3.30	3.55	3.85	V
	Voltage detection level Vdet1_A (2)	At the falling of V_{CC}	3.45	3.70	4.00	V
	Voltage detection level Vdet1_B (2)	At the falling of V_{CC}	3.60	3.85	4.15	V
	Voltage detection level Vdet1_C (2)	At the falling of V_{CC}	3.75	4.00	4.30	V
	Voltage detection level Vdet1_D (2)	At the falling of V_{CC}	3.90	4.15	4.45	V
	Voltage detection level Vdet1_E (2)	At the falling of V_{CC}	4.05	4.30	4.60	V
	Voltage detection level Vdet1_F (2)	At the falling of V_{CC}	4.20	4.45	4.75	V
—	Hysteresis width at the rising of V_{CC} in voltage detection 1 circuit	Vdet1_0 to Vdet1_5 selected	—	0.07	—	V
		Vdet1_6 to Vdet1_F selected	—	0.10	—	V
—	Voltage detection 1 circuit response time (3)	At the falling of V_{CC} from 5.0 V to (Vdet1_0 – 0.1) V	—	60	150	µs
—	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	—	1.7	—	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (4)		—	—	100	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version).
2. Select the voltage detection level with bits VD1S0 to VD1S3 in the VD1LS register.
3. Time until the voltage monitor 1 interrupt request is generated after the voltage passes V_{det1}.
4. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.

Table 5.12 High-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
—	High-speed on-chip oscillator frequency after reset	V_{CC} = 1.8 V to 5.5 V −20 °C ≤ Topr ≤ 85 °C	38.4	40	41.6	MHz
		V_{CC} = 1.8 V to 5.5 V −40 °C ≤ Topr ≤ 85 °C	38.0	40	42.0	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register (2)	V_{CC} = 1.8 V to 5.5 V −20 °C ≤ Topr ≤ 85 °C	35.389	36.864	38.338	MHz
		V_{CC} = 1.8 V to 5.5 V −40 °C ≤ Topr ≤ 85 °C	35.020	36.864	38.707	MHz
	High-speed on-chip oscillator frequency when the FRA6 register correction value is written into the FRA1 register and the FRA7 register correction value into the FRA3 register	V_{CC} = 1.8 V to 5.5 V −20 °C ≤ Topr ≤ 85 °C	30.72	32	33.28	MHz
		V_{CC} = 1.8 V to 5.5 V −40 °C ≤ Topr ≤ 85 °C	30.40	32	33.60	MHz
—	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	0.5	3	ms
—	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	400	—	µA

Notes:
1. V_{CC} = 1.8 to 5.5 V and T_{opr} = −20 to 85 °C (N version)/−40 to 85 °C (D version), unless otherwise specified.
2. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.13 Low-speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		60	125	250	kHz
—	Oscillation stability time	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	30	100	µs
—	Self power consumption at oscillation	V_{CC} = 5.0 V, T_{opr} = 25 °C	—	2	—	µA

Note:
1. V_{CC} = 1.8 to 5.5 V and T_{opr} = −20 to 85 °C (N version)/−40 to 85 °C (D version), unless otherwise specified.

Table 5.14 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on (2)		—	—	2,000	µs

Notes:
1. The measurement condition is V_{CC} = 1.8 to 5.5 V and T_{opr} = 25 °C.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.

Table 5.17 Electrical Characteristics (1) [4.2 V ≤ Vcc ≤ 5.5 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output "H" voltage	Other than XOUT	Drive capacity High V_{CC} = 5 V	I_{OH} = –20 mA	V_{CC} – 2.0	—	V_{CC}	V
			Drive capacity Low V_{CC} = 5 V	I_{OH} = –5 mA	V_{CC} – 2.0	—	V_{CC}	V
		XOUT	V_{CC} = 5 V	I_{OH} = –200 µA	1.0	—	V_{CC}	V
V_{OL}	Output "L" voltage	Other than XOUT	Drive capacity High V_{CC} = 5 V	I_{OL} = 20 mA	—	—	2.0	V
			Drive capacity Low V_{CC} = 5 V	I_{OL} = 5 mA	—	—	2.0	V
		XOUT	V_{CC} = 5 V	I_{OL} = 200 µA	—	—	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT4}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRDIOA0, TRDIOB0, TRDIOC0, TRDIOD0, TRDIOA1, TRDIOB1, TRDIOC1, TRDIOD1, TRCTRG, TRCCLK, TRFI, $\overline{TRGIOA}$, $\overline{TRGIOB}$, $\overline{ADTRG}$, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.1	1.2	—	V
		$\overline{RESET}$			0.1	1.2	—	V
I_{IH}	Input "H" current		V_I = 5 V, V_{CC} = 5.0 V		—	—	5.0	µA
I_{IL}	Input "L" current		V_I = 0 V, V_{CC} = 5.0 V		—	—	–5.0	µA
R_{PULLUP}	Pull-up resistance		V_I = 0 V, V_{CC} = 5.0 V		25	50	100	kΩ
R_{fXIN}	Feedback resistance	XIN			—	0.3	—	MΩ
R_{fXCIN}	Feedback resistance	XCIN			—	8	—	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Note:
1. 4.2 V ≤ V_{CC} ≤ 5.5 V, T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version), and f(XIN) = 20 MHz, unless otherwise specified.

Table 5.22 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	200	—	ns
$t_{W(CKH)}$	CLKi input “H” width	100	—	ns
$t_{W(CKL)}$	CLKi input “L” width	100	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	50	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	50	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

i = 0 to 2

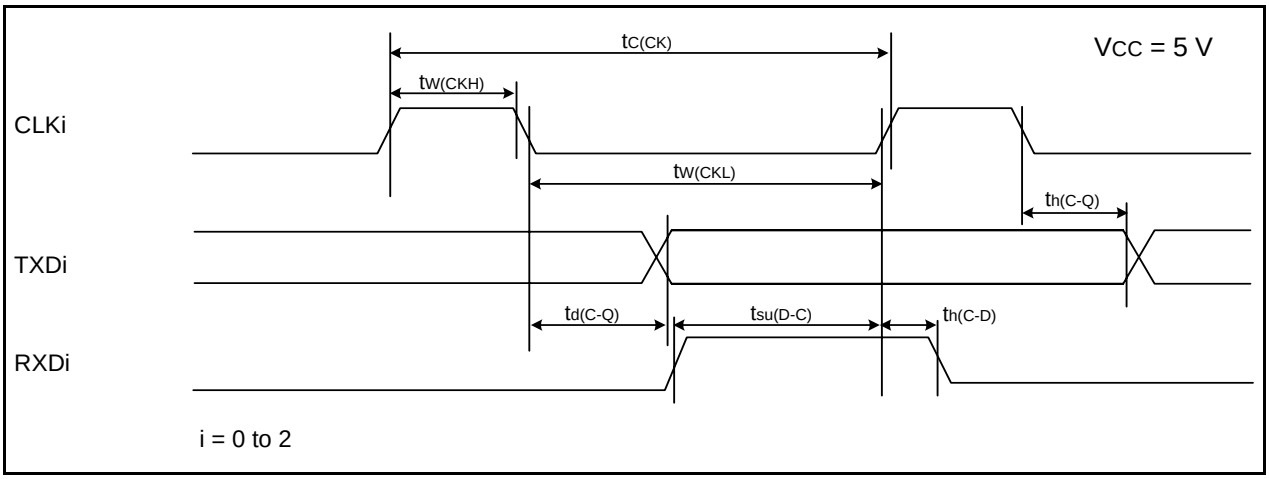


Figure 5.11 Serial Interface Timing Diagram when V_{CC} = 5 V

Table 5.23 External Interrupt $\overline{INTi}$ (i = 0 to 4) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	250 (1)	—	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	250 (2)	—	ns

Notes:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

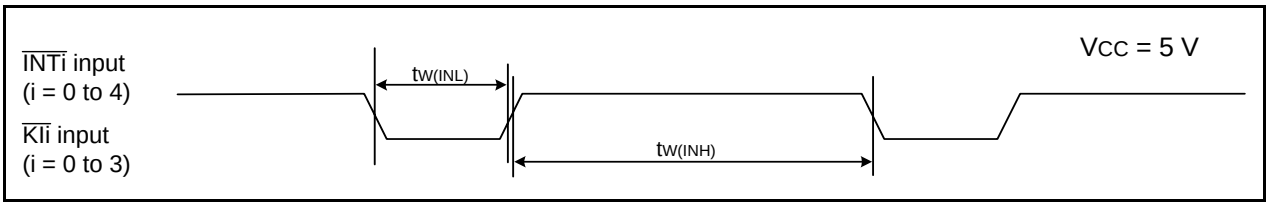


Figure 5.12 Input Timing Diagram for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{KIi}$ when V_{CC} = 5 V

Table 5.25 Electrical Characteristics (4) [2.7 V ≤ Vcc ≤ 3.3 V]
(Topr = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
Icc	Power supply current (Vcc = 2.7 to 3.3 V) Single-chip mode, output pins are open, other pins are Vss	High-speed clock mode	XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz No division	—	3.5	10	mA
			XIN = 10 MHz (square wave) High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	1.5	7.5	mA
		High-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz No division	—	7.0	15	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 20 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	3.0	—	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz No division	—	4.0	—	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 10 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-8	—	1.5	—	mA
			XIN clock off High-speed on-chip oscillator on fOCO-F = 4 MHz Low-speed on-chip oscillator on = 125 kHz Divide-by-16, MSTIIC = MSTTRD = MSTTRC = 1	—	1	—	mA
		Low-speed on-chip oscillator mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz Divide-by-8, FMR27 = 1, VCA20 = 0	—	90	390	µA
		Low-speed clock mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division FMR27 = 1, VCA20 = 0	—	80	400	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz No division Program operation on RAM Flash memory off, FMSTP = 1, VCA20 = 0	—	40	—	µA
		Wait mode	XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock operation VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	15	90	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator on = 125 kHz While a WAIT instruction is executed Peripheral clock off VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	4	80	µA
			XIN clock off High-speed on-chip oscillator off Low-speed on-chip oscillator off XCIN clock oscillator on = 32 kHz (peripheral clock off) While a WAIT instruction is executed VCA27 = VCA26 = VCA25 = 0, VCA20 = 1	—	3.5	—	µA
		Stop mode	XIN clock off, Topr = 25 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	2.0	5.0	µA
			XIN clock off, Topr = 85 °C High-speed on-chip oscillator off Low-speed on-chip oscillator off CM10 = 1 Peripheral clock off VCA27 = VCA26 = VCA25 = 0	—	15	—	µA

Table 5.31 Electrical Characteristics (5) [1.8 V ≤ Vcc < 2.7 V]

Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Other than XOUT	Drive capacity High	I_{OH} = –2 mA	V_{CC} – 0.5	—	V_{CC}	V
			Drive capacity Low	I_{OH} = –1 mA	V_{CC} – 0.5	—	V_{CC}	V
		XOUT		I_{OH} = –200 μA	1.0	—	V_{CC}	V
V_{OL}	Output “L” voltage	Other than XOUT	Drive capacity High	I_{OL} = 2 mA	—	—	0.5	V
			Drive capacity Low	I_{OL} = 1 mA	—	—	0.5	V
		XOUT		I_{OL} = 200 μA	—	—	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT4}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, TRBO, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRDIOA0, TRDIOB0, TRDIOC0, TRDIOD0, TRDIOA1, TRDIOB1, TRDIOC1, TRDIOD1, TRCTRG, TRCCLK, TRFI, $\overline{TRGIOA}$, TRGIOB, $\overline{ADTRG}$, RXD0, RXD1, RXD2, CLK0, CLK1, CLK2, SSI, SCL, SDA, SSO			0.05	0.20	—	V
		$\overline{RESET}$			0.05	0.20	—	V
I_{IH}	Input “H” current		V_I = 2.2 V, V_{CC} = 2.2 V		—	—	4.0	μA
I_{IL}	Input “L” current		V_I = 0 V, V_{CC} = 2.2 V		—	—	–4.0	μA
R_{PULLUP}	Pull-up resistance		V_I = 0 V, V_{CC} = 2.2 V		70	140	300	kΩ
R_{fXIN}	Feedback resistance	XIN			—	0.3	—	MΩ
R_{fXCIN}	Feedback resistance	XCIN			—	8	—	MΩ
V_{RAM}	RAM hold voltage		During stop mode		1.8	—	—	V

Note:
1. 1.8 V ≤ V_{CC} < 2.7 V, T_{opr} = –20 to 85 °C (N version)/–40 to 85 °C (D version), and f(XIN) = 5 MHz, unless otherwise specified.

Timing requirements (Unless Otherwise Specified: V_{CC} = 2.2 V, V_{SS} = 0 V, T_{opr} = 25 °C)

Table 5.33 External Clock Input (XOUT, XCIN)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XOUT)}$	XOUT input cycle time	200	—	ns
$t_{WH(XOUT)}$	XOUT input “H” width	90	—	ns
$t_{WL(XOUT)}$	XOUT input “L” width	90	—	ns
$t_{c(XCIN)}$	XCIN input cycle time	14	—	µs
$t_{WH(XCIN)}$	XCIN input “H” width	7	—	µs
$t_{WL(XCIN)}$	XCIN input “L” width	7	—	µs

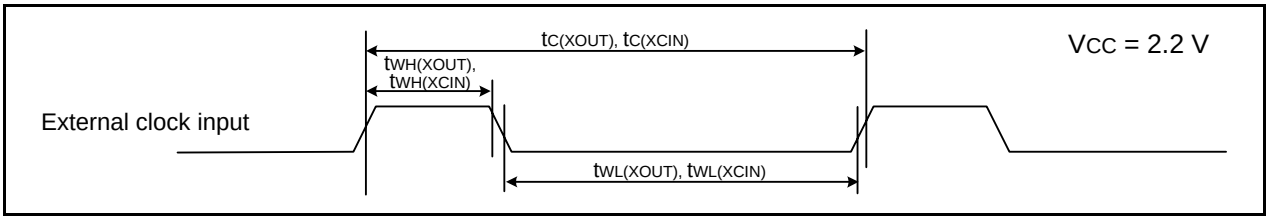


Figure 5.18 External Clock Input Timing Diagram when V_{CC} = 2.2 V

Table 5.34 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	500	—	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	200	—	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	200	—	ns

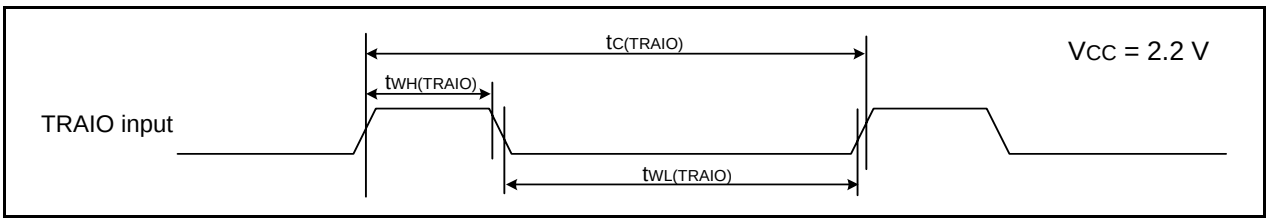


Figure 5.19 TRAIO Input Timing Diagram when V_{CC} = 2.2 V

Table 5.35 TRFI Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRFI)}$	TRFI input cycle time	2000 (1)	—	ns
$t_{WH(TRFI)}$	TRFI input “H” width	1000 (2)	—	ns
$t_{WL(TRFI)}$	TRFI input “L” width	1000 (2)	—	ns

Notes:
1. When using timer RF input capture mode, adjust the cycle time to (1/timer RF count source frequency × 3) or above.
2. When using timer RF input capture mode, adjust the pulse width to (1/timer RF count source frequency × 1.5) or above.

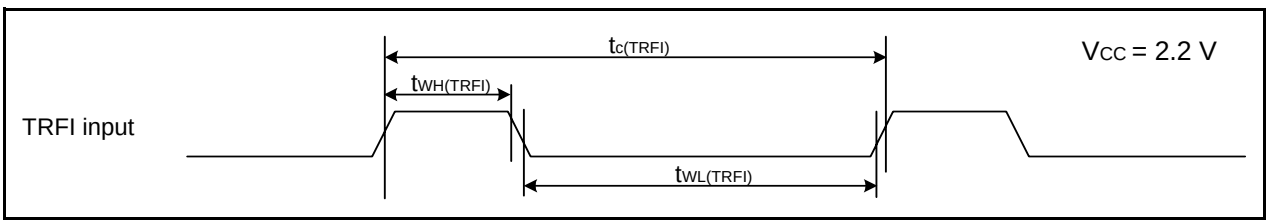


Figure 5.20 TRFI Input Timing Diagram when V_{CC} = 2.2 V

Table 5.36 Serial Interface

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(CK)}$	CLKi input cycle time	800	—	ns
$t_{W(CKH)}$	CLKi input “H” width	400	—	ns
$t_{W(CKL)}$	CLKi input “L” width	400	—	ns
$t_{d(C-Q)}$	TXDi output delay time	—	200	ns
$t_{h(C-Q)}$	TXDi hold time	0	—	ns
$t_{su(D-C)}$	RXDi input setup time	150	—	ns
$t_{h(C-D)}$	RXDi input hold time	90	—	ns

i = 0 to 2

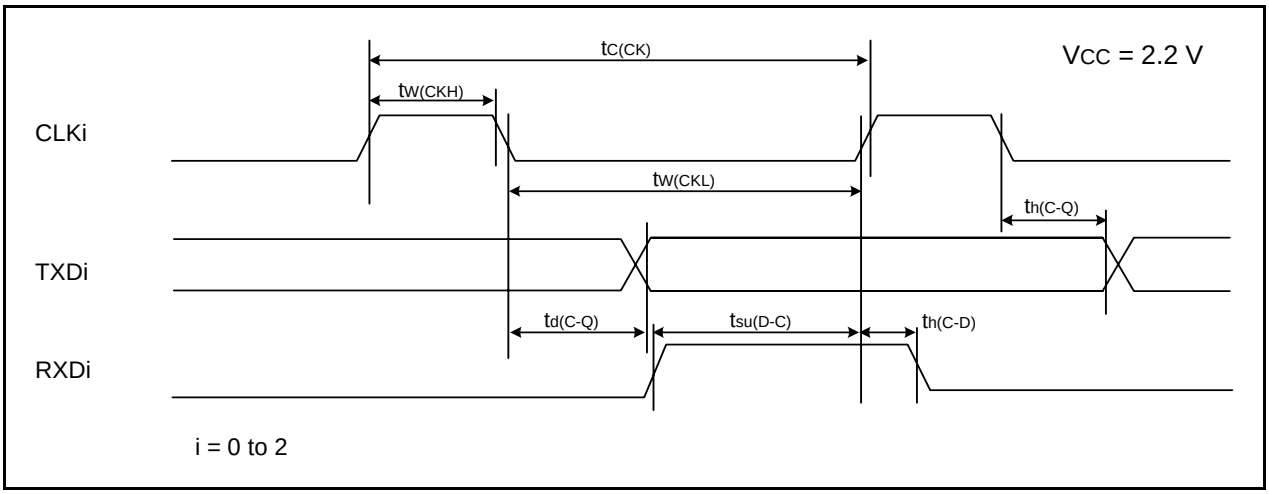


Figure 5.21 Serial Interface Timing Diagram when Vcc = 2.2 V

Table 5.37 External Interrupt $\overline{INTi}$ (i = 0 to 4) Input, Key Input Interrupt $\overline{KIi}$ (i = 0 to 3)

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{W(INH)}$	$\overline{INTi}$ input “H” width, $\overline{KIi}$ input “H” width	1000 (1)	—	ns
$t_{W(INL)}$	$\overline{INTi}$ input “L” width, $\overline{KIi}$ input “L” width	1000 (2)	—	ns

Notes:
1. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input HIGH width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.
2. When selecting the digital filter by the $\overline{INTi}$ input filter select bit, use an $\overline{INTi}$ input LOW width of either (1/digital filter clock frequency × 3) or the minimum value of standard, whichever is greater.

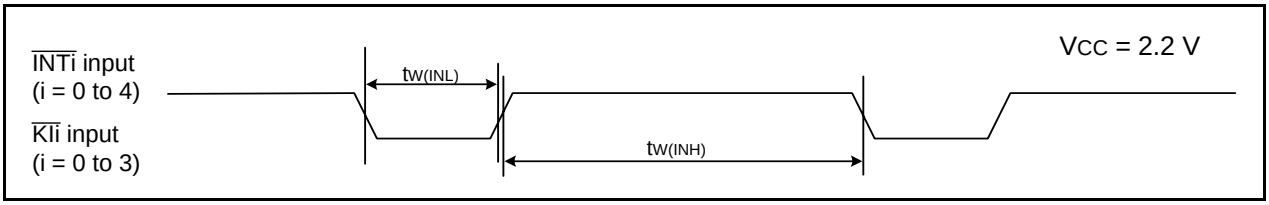


Figure 5.22 Input Timing Diagram for External Interrupt $\overline{INTi}$ and Key Input Interrupt $\overline{KIi}$ when Vcc = 2.2 V

REVISION HISTORY	R8C/38C Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.01	Oct 30, 2009	—	First Edition issued
1.00	Apr 23, 2010	All pages	“Preliminary”, “Under development” deleted
		4	Table 1.3 revised
		27 to 53	“5. Electrical Characteristics” added
1.10	Nov 02, 2010	—	TN-R8C-A015A/E reflected
		3	Table 1.2 “Timer RG” revised
		4	Table 1.3 revised
		5	Figure 1.1 revised
		15	Figure 3.1 revised
		31	Table 5.3 “tCONV”, “tSAMP” revised
		45	Table 5.21 revised
		49	Table 5.28 revised
		53	Table 5.35 revised